

■ Features

- High Output Power: $P_{sat}=55.8\text{dBm}$ (Typ.)
- High Gain: $G_p=13.8\text{dB}$ (Typ.)
- High Drain Efficiency: $DE=50\%$ (Typ.)
- Broad Band: 5.2 to 5.9GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\text{ohm}$
- Hermetically Sealed Package

■ Description

The SGC5259-300A-R is a high power GaN-HEMT that is internally matched for C-band radar bands to provide optimum power and gain in a 50ohm system.



ABSOLUTE MAXIMUM RATING (Case Temperature $T_c=25\text{ deg.C}$)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	55	V
Gate-Source Voltage	V_{GS}	-15	V
Storage Temperature	T_{stg}	-55 to +125	deg.C
Channel Temperature	T_{ch}	+250	deg.C

RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
Drain-Source Voltage	V_{DS}		≤ 50	V
Forward Gate Current	I_{GF}	$R_g=10\text{ohm}$	≤ 187.2	mA
Reverse Gate Current	I_{GR}	$R_g=10\text{ohm}$	≥ -13.6	mA
Channel Temperature	T_{ch}		$< +200$	deg.C

ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25\text{ deg.C}$)

Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-off Voltage	V_p	$V_{DS}=50\text{V}$, $I_{DS}=20.0\text{mA}$	-	-4.5	-	V
Frequency Range	Freq.	$V_{DS}=50\text{V}$	5.2	-	5.9	GHz
Output Power *1	P_{sat}	$I_{DS(DC)}=1.0\text{A}$	54.8	55.8	-	dBm
Output Power *2	P_{sat}	Pulse Width=100μsec.	54.5	55.4	-	dBm
Power Gain *1	G_p	Duty=10%	12.8	13.8	-	dB
Power Gain *2	G_p	*1: $f=5.2$ to 5.7GHz	12.5	13.4	-	dB
Drain Current	I_{DSR}	*2: $f=5.7$ to 5.9GHz	-	15.2	-	A
Drain Efficiency	DE	Pin=42dBm	-	50	-	%
Thermal Resistance	R_{th}	Channel to Case ($P_{diss}=100\text{W}$, CW)	-	0.7	0.8	deg.C/W

CASE STYLE	IK		
RoHS Compliance	YES		
ESD	Class 2	2000V to <4000V	

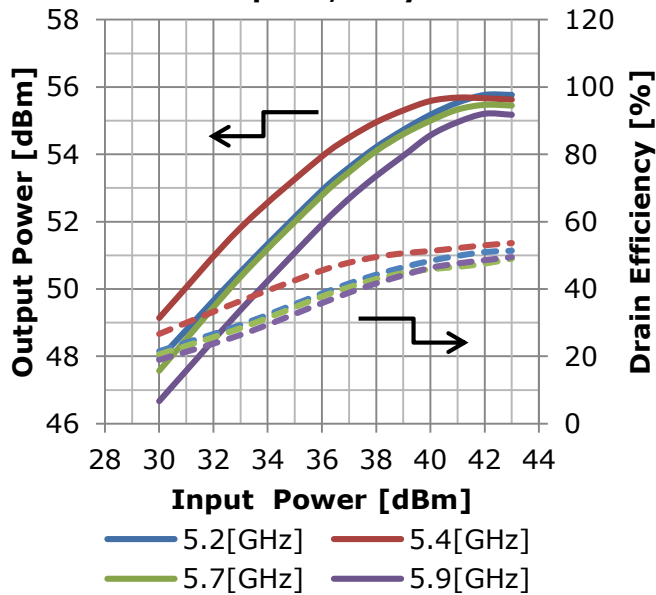
Note: Based on ANSI/ESDA/JEDEC JS-001-2012($C=100\text{pF}$, $R=1.5\text{kohm}$)



● **RF Characteristics**

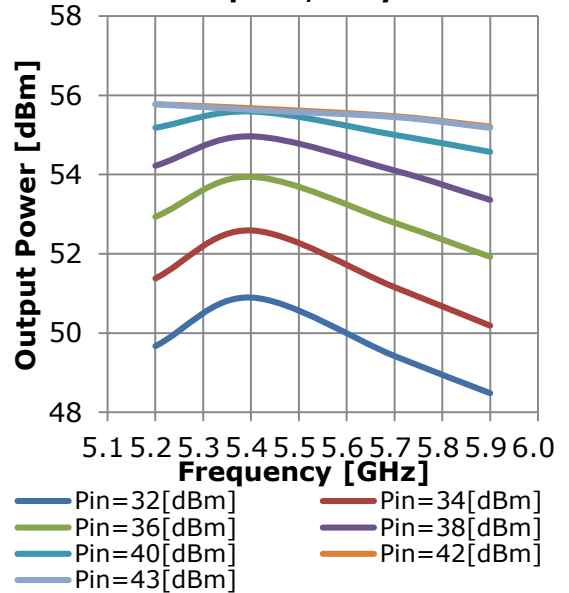
**Output Power &
Drain Efficiency vs. Input Power**

$V_{DS}=50V$, $I_{DS(DC)}=1.0A$
 $PW=100\mu sec.$, Duty=10%



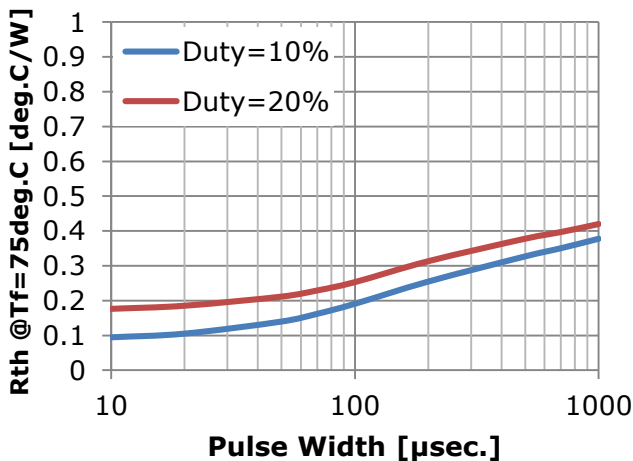
Output Power vs. Frequency

$V_{DS}=50V$, $I_{DS(DC)}=1.0A$
 $PW=100\mu sec.$, Duty=10%

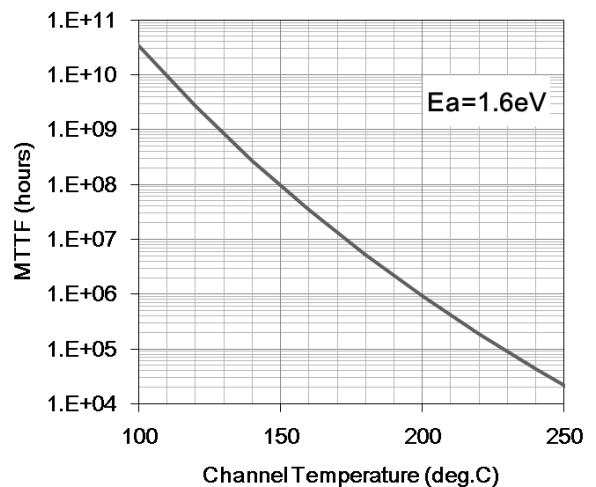


● **Thermal Characteristics In Pulsed Operation**

Rth vs. Pulse Width



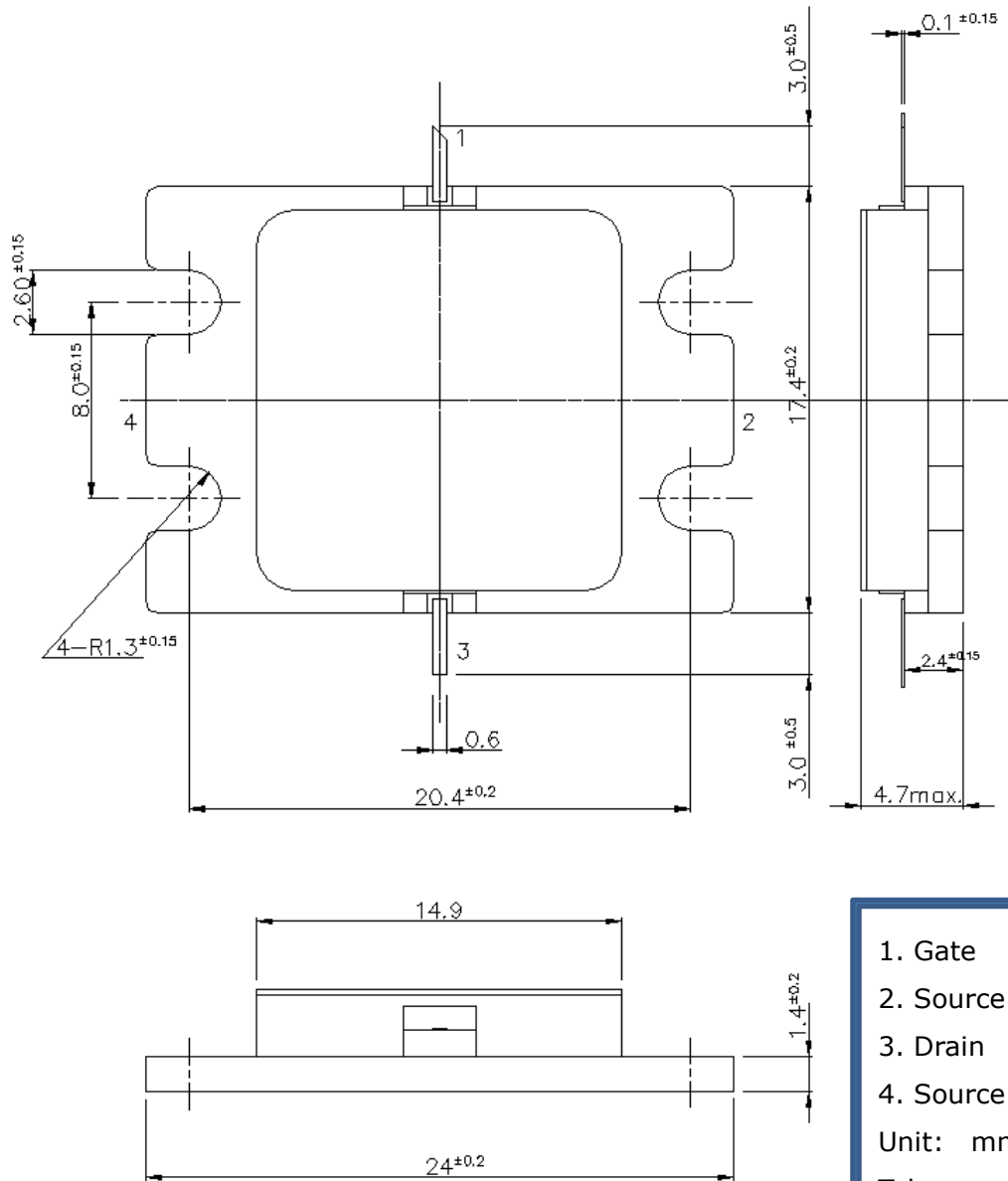
MTTF vs. Tch





● **Package Outline**

Case Style : IK



1. Gate
2. Source
3. Drain
4. Source
Unit: mm
Tolerance: \pm 0.15

For Safety, Observe the Following Procedures Environmental Management

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Respect all applicable laws of the country when discarding this product.
This product must be disposed in accordance with methods specified by applicable hazardous waste procedures.

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